

L Number	Hits	Search Text	DB	Time stamp
1	1	10/666649	USPAT; US-PGPUB	2004/10/27 08:04
3	33	(mask\$ near5 (wafer substrate workpiece)) with ((separat\$4 with (rota\$6))	USPAT; US-PGPUB	2004/10/27 08:09
4	80	(mask\$3 near5 (wafer substrate workpiece)) with ((separat\$4 remov\$5 divid\$5) with (rota\$6))	USPAT; US-PGPUB	2004/10/27 08:15
5	8	semiconductor with (mask\$3 near5 (wafer substrate workpiece)) with ((separat\$4 remov\$5 divid\$5) with (rota\$6))	USPAT; US-PGPUB	2004/10/27 08:21
6	26875	(semiconductor near4 (wafer substrate workpiece)) with (mask\$3 photoresist resist)	USPAT; US-PGPUB	2004/10/27 08:23
7	2217	((semiconductor near4 (wafer substrate workpiece)) with (mask\$3 photoresist resist)) and ((semiconductor near4 (wafer substrate workpiece)) with (rotat\$4 spin\$4))	USPAT; US-PGPUB	2004/10/27 08:27
8	1065	((((semiconductor near4 (wafer substrate workpiece)) with (mask\$3 photoresist resist)) and ((semiconductor near4 (wafer substrate workpiece)) with (rotat\$4 spin\$4))) and ((semiconductor near4 (wafer substrate workpiece)) with (separat\$4 remov\$5 divid\$4)))	USPAT; US-PGPUB	2004/10/27 08:26
9	479	(((((semiconductor near4 (wafer substrate workpiece)) with (mask\$3 photoresist resist)) and ((semiconductor near4 (wafer substrate workpiece)) with (rotat\$4 spin\$4))) and ((semiconductor near4 (wafer substrate workpiece)) with (separat\$4 remov\$5 divid\$4))) and ((mask\$3 photoresist resist) with (rotat\$4 spin\$4)))	USPAT; US-PGPUB	2004/10/27 08:29
11	8	((((((semiconductor near4 (wafer substrate workpiece)) with (mask\$3 photoresist resist)) and ((semiconductor near4 (wafer substrate workpiece)) with (rotat\$4 spin\$4))) and ((semiconductor near4 (wafer substrate workpiece)) with (separat\$4 remov\$5 divid\$4))) and ((mask\$3 photoresist resist) with (rotat\$4 spin\$4))) and (separat\$ near\$3 device)) and (wedge)	USPAT; US-PGPUB	2004/10/27 08:31
10	450	(((((semiconductor near4 (wafer substrate workpiece)) with (mask\$3 photoresist resist)) and ((semiconductor near4 (wafer substrate workpiece)) with (rotat\$4 spin\$4))) and ((semiconductor near4 (wafer substrate workpiece)) with (separat\$4 remov\$5 divid\$4))) and ((mask\$3 photoresist resist) with (rotat\$4 spin\$4))) and (separat\$ near\$3 device)	USPAT; US-PGPUB	2004/10/27 08:44
12	467	((((((semiconductor near4 (wafer substrate workpiece)) with (mask\$3 photoresist resist)) and ((semiconductor near4 (wafer substrate workpiece)) with (rotat\$4 spin\$4))) and ((semiconductor near4 (wafer substrate workpiece)) with (separat\$4 remov\$5 divid\$4))) and ((mask\$3 photoresist resist) with (rotat\$4 spin\$4))) and (separat\$ near\$3 device)	USPAT; US-PGPUB	2004/10/27 08:47
13	273	((((((semiconductor near4 (wafer substrate workpiece)) with (mask\$3 photoresist resist)) and ((semiconductor near4 (wafer substrate workpiece)) with (rotat\$4 spin\$4))) and ((semiconductor near4 (wafer substrate workpiece)) with (separat\$4 remov\$5 divid\$4))) and ((mask\$3 photoresist resist) with (rotat\$4 spin\$4))) and (separat\$ near\$3 device)) and rotat\$4	USPAT; US-PGPUB	2004/10/27 08:45
14	17	((((((semiconductor near4 (wafer substrate workpiece)) with (mask\$3 photoresist resist)) and ((semiconductor near4 (wafer substrate workpiece)) with (rotat\$4 spin\$4))) and ((semiconductor near4 (wafer substrate workpiece)) with (separat\$4 remov\$5 divid\$4))) and ((mask\$3 photoresist resist) with (rotat\$4 spin\$4))) and (separat\$ near device)	USPAT; US-PGPUB	2004/10/27 08:47
15	22	(((((semiconductor near4 (wafer substrate workpiece)) with (mask\$3 photoresist resist)) and ((semiconductor near4 (wafer substrate workpiece)) with (rotat\$4 spin\$4))) and ((semiconductor near4 (wafer substrate workpiece)) with (separat\$4 remov\$5 divid\$4))) and ((mask\$3 photoresist resist) with (rotat\$4 spin\$4))) and (separat\$ near device wedge adj shap\$3)	USPAT; US-PGPUB	2004/10/27 08:57
16	61	"3691694"	USPAT; US-PGPUB	2004/10/27 08:57